

# 2N5962 Datasheet



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DiGi Electronics Part Number 2N5962-DG

Manufacturer onsemi

Manufacturer Product Number 2N5962

Description TRANS NPN 45V 0.1A TO92-3

Detailed Description Bipolar (BJT) Transistor NPN 45 V 100 mA 625 mW T

hrough Hole TO-92-3



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
2N5962	onsemi
Series:	Product Status:
	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
NPN	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
45 V	200mV @ 500μA, 10mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
2nA (ICBO)	600 @ 10mA, 5V
Power - Max:	Frequency - Transition:
625 mW	
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA)	TO-92-3
Base Product Number:	
2N5962	

# **Environmental & Export classification**

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
FAR99	8541 21 0095



#### Discrete POWER & Signal **Technologies**

### 2N5962







#### **NPN General Purpose Amplifier**

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	8.0	V
Ic	Collector Current - Continuous	100	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	М	Units	
		2N5962	*MMBT5962	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

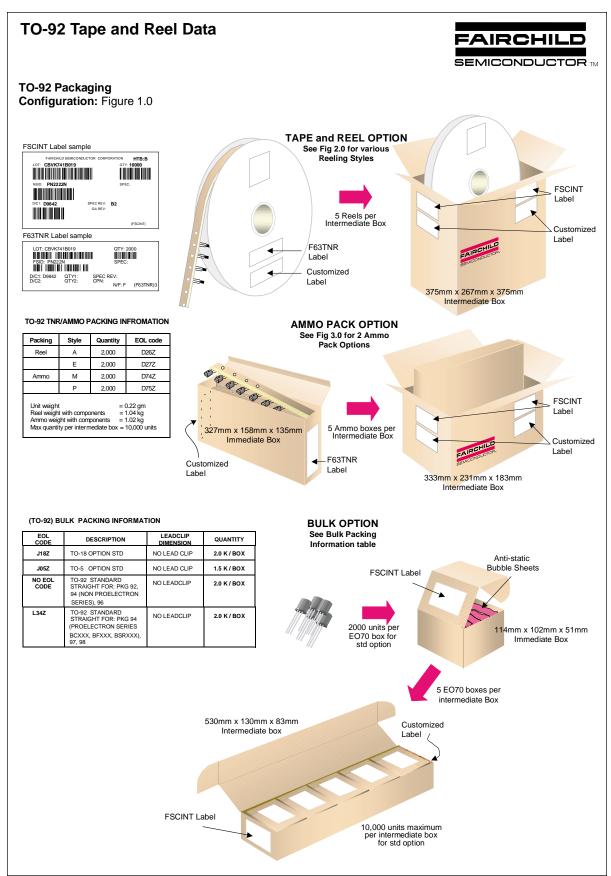
<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	45	I	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	45		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	8.0		V
СВО	Collector Cutoff Current	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0, T <sub>A</sub> = 65 °C		2.0 50	nA nA
EBO	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		1.0	nA
		$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$	500 550 600	1400	
ON CHAF	RACTERISTICS*				
		$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$			
	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	0.5	0.2	V
V <sub>CE(sat)</sub> V <sub>BE(on)</sub>	Collector-Emitter Saturation Voltage  Base-Emitter On Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$	0.5	0.2	V
SMALL S	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$	0.5	4.0	V
SMALL S	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	600	0.7	V
SMALL S Ccb Ceb	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	600	4.0 6.0	V
SMALL S	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \ I_C = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_C = 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_C = 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 10  \mu\text{A}, \\ &R_S = 10  k\Omega, \ f = 1.0  k\text{Hz}, \\ &B_W = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &R_S = 1.0  k\Omega, \ f = 1.0  k\text{Hz}, \\ &B_W = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &R_S = 1.0  k\Omega, \ f = 1.0  k\text{Hz}, \\ &B_W = 400 \text{ Hz}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &R_S = 1.0  k\Omega, \ f = 1.0  k\text{Hz}, \\ &R_W = 400 \text{ Hz}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 5.0 \text{ V}, \ I_C = 100  \mu\text{A}, \\ &V_{CE} = 100  \mu\text{A}, \\$	600	0.7 4.0 6.0 200	pF pF
SMALL S	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CB} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &R_{W} = 400 \text{ Hz}, \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{C} = 5.0 V, I_{C} = 100 \mu\text{A}, \\ &R_{C} = 100 \mu\text{A}$	600	0.7 4.0 6.0 200	pF pF
V <sub>BE(On)</sub>	Base-Emitter On Voltage  BIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CB} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ \end{split}$	600	0.7 4.0 6.0 200 3.0 6.0	pF pF dB

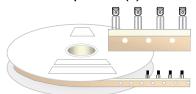
<sup>\*</sup>Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$ 



#### TO-92 Tape and Reel Data, continued

#### **TO-92 Reeling Style** Configuration: Figure 2.0

#### Machine Option "A" (H)

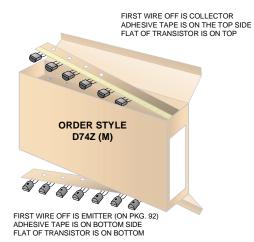


Style "A", D26Z, D70Z (s/h)

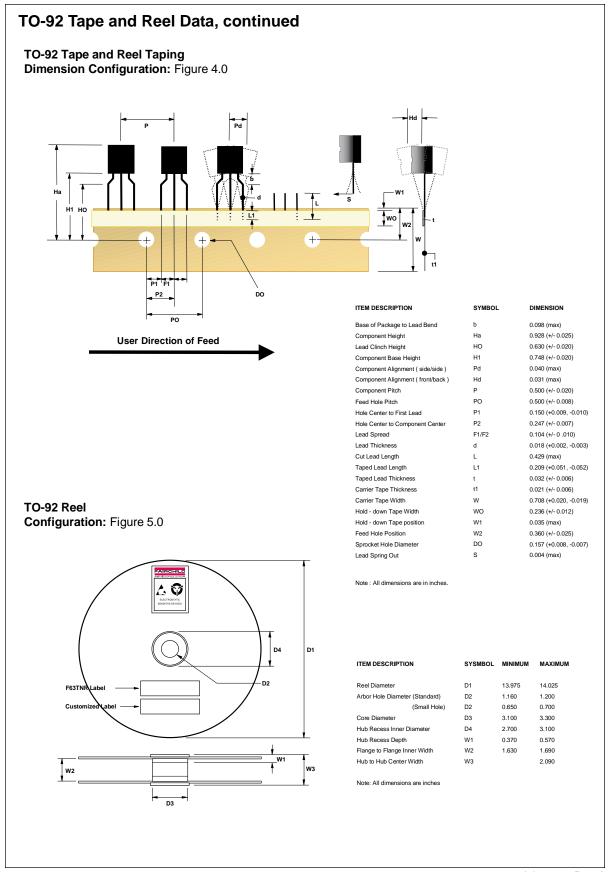
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

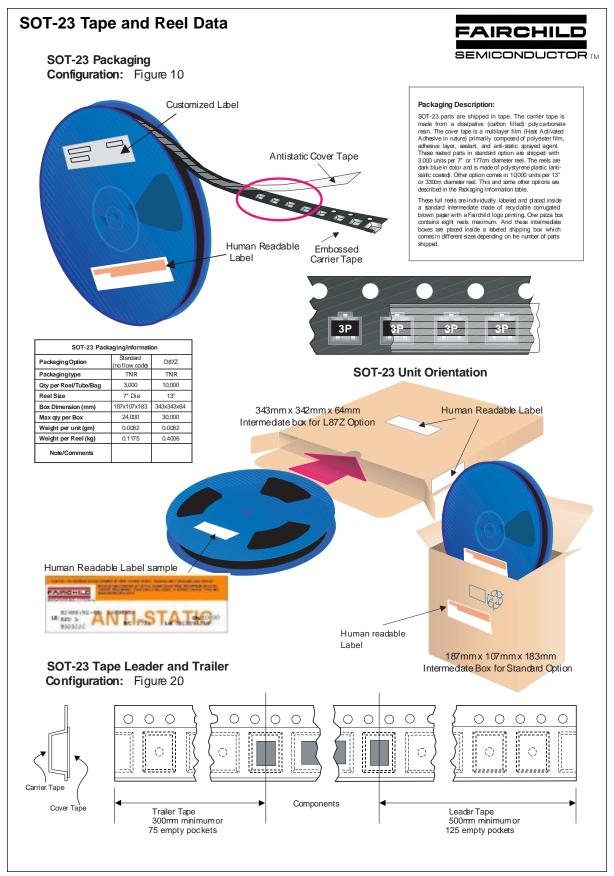
#### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0







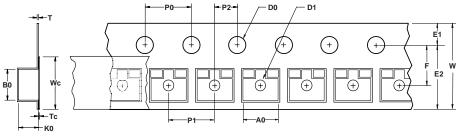
# **TO-92 Package Dimensions** SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 В В B F В D 2 В S С G Ε D Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.



#### SOT-23 Tape and Reel Data, continued

#### **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



User Direction of Feed	

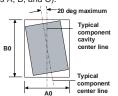
	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

SOT-23 Reel Configuration: Figure 4.0



Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

# Dim A Max Dim N To Diameter Option

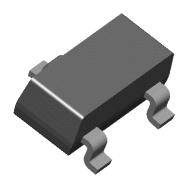
х		Dim N		I
			7'	Diameter Option
		<b>/</b>	_	B Min
	s	ee detail AA	Dim D	Dim C
		<del>  →</del>   W3	min	
	13" Diameter Option	W2 max Measured at Hub		
				DETAIL AA

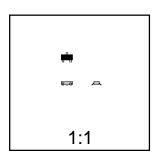
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

#### **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

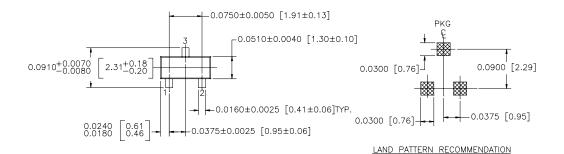


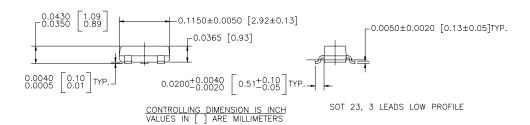


Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE : UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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DOME™ ISOPLANAR™ Quiet Series™ E²CMOS™ MICROWIRF™ SII FNT SWITC

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS

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Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.



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